Samsung V-NAND SSD 990 PRO

2022 Data Sheet

Revision 1.0



LEGAL DISCLAIMER

SAMSUNG ELECTRONICS CO., LTD. RESERVES THE RIGHT TO CHANGE PRODUCTS, INFORMATION AND SPECIFICATIONS WITHOUT NOTICE.

Products and specifications discussed herein are provided for reference purposes only. All information discussed herein may change without notice and is provided on an "AS IS" basis, without warranties of any kind. This document and all information discussed herein remain the sole and exclusive property of Samsung Electronics Co., Ltd. No license of any patent, copyright, mask work, trademark or any other intellectual property right is granted under this document, by implication, estoppels or otherwise. Samsung products are not intended for use in life support, critical care, medical, safety equipment, or similar applications where product failure could result in loss of life or personal or physical harm, or any military or defense application, or any governmental procurement to which special terms or provisions may apply. For updates or additional information about Samsung products, contact your nearest Samsung representative. All brand names, trademarks and registered trademarks belong to their respective owners.

COPYRIGHT © 2022

This material is copyrighted by Samsung Electronics Co., Ltd. Any unauthorized reproductions, use or disclosure of this material, or any part thereof, is strictly prohibited and is a violation under copyright law.

TRADEMARKS & SERVICE MARKS

The Samsung logo is the trademark of Samsung Electronics Co., Ltd. All other company and product names may be trademarks of the respective companies with which they are associated.

For more information, please visit www.samsung.com/ssd and www.samsungssd.com. To download the latest software & manuals, please visit www.samsung.com/samsungssd

TECHNICAL SPECIFICATIONS

	Samsı	ang SSD 990 PRO		
Client PCs, PlayStation®5				
PCIe Gen 4.0 x4, NVMe 2.0				
Capacity ¹⁾		1TB	2TB	
Controller		Samsung in-house Controller		
NAND Flash Memory		Samsung V-NAND TLC		
DRAM Cache Memory		1GB LPDDR4	2GB LPDDR4	
Dimension		Max 80.0 x Max 22 x Max 2.3 (mm)		
Form Factor		M,2 (2280)		
Sequential Read		7,450 MB/s	7,450 MB/s	
Sequential Write		6,900 MB/s	6,900 MB/s	
QD 1	Ran. Read	22K IOPS	22K IOPS	
Thread 1	Ran. Write	80K IOPS	80K IOPS	
QD 32 Thread 16	Ran. Read	1,200K IOPS	1400K IOPS	
	Ran. Write	1,550K IOPS	1,550K IOPS	
Idle (APST on)		50mW	55mW	
Active (Avg.)	Read	5.4 W	5.8W	
	Write	5.0 W	5.1W	
L1.2 mode		5 mW		
Temp.	Operating	0°C to 70°C (Measured by S.M.A.R.T. Temperature Proper airflow recommended)		
	Non-Operating	-40°C to 85°C		
Humidity		5% to 95% non-condensing		
Shock	Non-Operating	1,500G(Gravity), duration: 0.5ms, 3 axis		
Vibration	Non-Operating	20~2,000	Hz, 20G	
MTBF		1.5 million hours		
TBW		600TB	1,200TB	
Period		5 years limited		
TRIM (Required OS support), Garbage Collection, S.M.A.R.T				
AES 256-bit Full Disk Encryption, TCG/Opal V2.0, Encrypted Drive (IEEE1667)				
	Co NAND F DRAM C Dir Form Seque Seque QD 1 Thread 1 QD 32 Thread 16 Idle (Active (Avg.) L1 Temp. Hu Shock Vibration	Capacity¹) Controller NAND Flash Memory DRAM Cache Memory Dimension Form Factor Sequential Read Sequential Write QD 1 Ran. Read Thread 1 Ran. Write QD 32 Ran. Read Thread 16 Ran. Write Idle (APST on) Active Read (Avg.) Write L1.2 mode Temp. Operating Non-Operating Wibration Non-Operating WTBF TBW Period TRIM (Requested	PCIe Gen 4.0 x4, NVMe 2.0	

^{1) 1}GB = 1,000,000,000 bytes by IDEMA. A certain portion of capacity may be used for system file and maintenance use, thus the actual available capacity may differ from the labeled capacity.

^{2) 990} PRO is backward compatible with PCIe 3.0.

³⁾ Sequential and random performance measurements are based on IOmeter1.1.0. Performance may vary based on SSD's firmware version, system hardware & configuration. Test System: AMD Ryzen 7 5800X 8-Core Processor CPU@3.80GHz, DDR4 3600MHz 16GBx2, OS-Windows 10 Pro 64bit, Chipset-ASRock-X570-Taichi

⁴⁾ Sequential and random write performance was measured with Intelligent TurboWrite technology being activated. Intelligent TurboWrite operates only within a specific data transfer size. For detailed information, please contact your local service center

⁵⁾ Power consumption is measured with IOmeter 1.1.0 version with AMD Ryzen 7 5800X 8-Core Processor CPU@3.80GHz, DDR4 3600MHz 16GBx2, OS-Windows 10 Pro 64bit, Chipset-ASRock-X570-Taichi

⁶⁾ All documented endurance test results are in compliance with JESD218 Standards. Please visit www.jedec.org for detailed information on JESD218 Standards. TBW means Terabytes Written, Warranty provides coverage for the stated time period or the TBW, whichever comes first. Please refer to the detailed warranty statement here at http://www.samsung.com/samsungssd

PRODUCT LINEUP

Density	Model Name	Box Contents	Model Code
1TB	MZ-V9P1T0	Samsung SSD 990 PRO 1TB	MZ-V9P1T0BW
(1,000GB*)	MZ-V9P110	Warranty Statement	MZ-V9P1T0B/AM
2TB	MZ-V9P2T0	Samsung SSD 990 PRO 2TB	MZ-V9P2T0BW
(2,000GB*) WZ-V9F2T0	Warranty Statement	MZ-V9P2T0B/AM	

 $^{^{*}}$ GB: 1GB = 1,000,000,000 bytes. The actual usable capacity may be less than the labeled capacity.

For more information, including but not limited to the warranty provided for this product, and to download the latest software & manuals, please visit www.samsung.com/ssd and www.samsungssd.com.

TEST CONFIGURATION

Below you will find a list of system configurations Samsung used to obtain the results reported in this Data Sheet. All performance data was measured with the SSD as a secondary drive

	Read/Write Performance	Power Consumption	
Interface	PCIe Gen 4.0 x4	PCIe Gen 4.0 x4	
OS	Windows 10 Pro 64bit	Windows 10 Pro 64bit	
СРИ	AMD Ryzen 7 5800X 8-Core CPU@3.80GHz	AMD Ryzen 7 5800X 8-Core CPU@3.80GHz	
Memory	DDR4 3600MHz 16GBx2	DDR4 3600MHz 16GBx2	
Chipset	ASRock-X570-Taichi	ASRock-X570-Taichi	
Test Program	IOmeter 1.1.0	IOmeter 1.1.0	

Revision History

Revision Number	Description	Revision Date
1.0	Initial Release	October, 2022